

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	4329183	(transistor) or (source drain gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/11 21:59
L2	321925	(semicondctor si silicon) with substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/11 22:00
L3	15502	plug and 1 and 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/11 22:01
L4	9841	(barrier tin ti tisin (titanium adj3 silicide adj3 nitride)) and 3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/11 22:02
L5	8333	4 and (tungsten w)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/11 22:03
L6	199	(intervention intervened intervening intermediate) and 5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/11 22:04